

**IN THE SPECIFICATION:**

**Paragraph beginning at line 3 of page 1 has been amended as follows:**

The present invention relates to a semiconductor device and a manufacturing method therefor and, in particular, to a MOS type transistor having a shallow high concentration junction for forming a source/drain region in a stable manner.

**Paragraph beginning at line 19 of page 2 has been amended as follows:**

a low concentration source/drain region of a reverse or opposite conductivity type formed in a region surrounded by the field oxide film and the gate electrode;

**Heading at line 21 of page 5 has been amended as follows:**

**DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS**

**Paragraph beginning at line 22 of page 5 has been amended as follows:**

With a semiconductor device according to the present invention, a MOS type transistor can be provided having a stable drain/source region, in which a high concentration region constituting the drain/source region is formed so

shallowly as to prevent the region from extending beyond a contact hole due to a production variation ~~etc.~~, for example.